

## PVsyst V7.2.5

DV	modu	_ م <b>ا</b>	DYI	MG_7	72H_	4በበ

Manufacturer Model	Generic DXM6-72H-400	Commercial data Availability: Prod. Since 2020		
Model	DXIVI0-72H-400	• • • •		
		Data source : Datas	sheets 2020	
Pnom STC power (manufacturer)	400 Wp	Technology	Si-mono	
Module size (W x L) 1.002	x 2.018 m <sup>2</sup>	Rough module area (Amodule)	2.02 m <sup>2</sup>	
Number of cells	2 x 72	Sensitive area (cells) (Acells)	1.79 m²	
Specifications for the model (manufa	cturer or measureme	ent data)		
Reference temperature (TRef)	25 °C	Reference irradiance (GRef)	1000 W/m <sup>2</sup>	
Open circuit voltage (Voc)	49.3 V	Short-circuit current (Isc)	10.30 A	
Max. power point voltage (Vmpp)	40.8 V	Max. power point current (Impp)	9.80 A	
=> maximum power (Pmpp)	399.8 W	Isc temperature coefficient (mulsc)	5.2 mA/°C	
One-diode model parameters				
Shunt resistance (Rshunt)	500 Ω	Diode saturation current (loRef)	0.016 nA	
Serie resistance (Rserie)	0.28 Ω	Voc temp. coefficient (MuVoc)	-167 mV/°C	
Specified Pmax temper. coeff. (muPMaxR)	-0.40 %/°C	Diode quality factor (Gamma)	0.98	
		Diode factor temper. coeff. (muGamma	-0.001 1/°C	
Reverse Bias Parameters, for use in l	behaviour of PV array	s under partial shadings or mismatch		
Reverse characteristics (dark) (BRev)	3.20 mA/V <sup>2</sup>	(quadratic factor (per cell))		
Number of by-pass diodes per module	3	Direct voltage of by-pass diodes	-0.7 V	
Model results for standard conditions	s (STC: T=25 °C, G=	:1000 W/m², AM=1.5)		
Max. power point voltage (Vmpp)	40.9 V	Max. power point current (Impp)	9.81 A	
Maximum power (Pmpp)	399.9 Wp	Power temper. coefficient (muPmpp)	-0.40 %/°C	
Efficiency(/ Module area) (Eff_mod)	19.8 %	Fill factor (FF)	0.788	
Efficiency(/ Cells area) (Eff cells)	22.4 %			

